DATA SHEET



NPN SILICON GERMANIUM RF TRANSISTOR NESG2101M16

NPN SiGE RF TRANSISTOR FOR MEDIUM OUTPUT POWER AMPLIFICATION (125 mW) 6-PIN LEAD-LESS MINIMOLD (M16, 1208 PKG)

FEATURES

The device is an ideal choice for medium output power, high-gain amplification and low distortion, low noise, high-gain amplification

Po (1 dB) = 21 dBm TYP. @
$$VcE = 3.6 \text{ V}$$
, Ic (set) = 10 mA (RF OFF), $f = 2 \text{ GHz}$ NF = 0.6 dB TYP., $Ga = 19.0 \text{ dB}$ TYP. @ $VcE = 2 \text{ V}$, $Ic = 7 \text{ mA}$, $f = 1 \text{ GHz}$

- Maximum stable power gain: MSG = 17.0 dB TYP. @ VcE = 3 V, Ic = 50 mA, f = 2 GHz
- High breakdown voltage technology for SiGe Tr. adopted: VCEO (absolute maximum ratings) = 5.0 V
- 6-pin lead-less minimold (M16, 1208 PKG)

<R> ORDERING INFORMATION

Part Number	Order Number	Package	Quantity	Supplying Form
NESG2101M16	NESG2101M16-A	6-pin lead-less minimold (M16, 1208 PKG)	50 pcs (Non reel)	8 mm wide embossed taping Pin 1 (Collector), Pin 6 (Emitter) face the
NESG2101M16-T3	NESG2101M16-T3-A	(Pb-Free)	10 kpcs/reel	perforation side of the tape

Remark To order evaluation samples, please contact your nearby sales office. Unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^{\circ}C$)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	Vcво	13.0	٧
Collector to Emitter Voltage	VCEO	5.0	٧
Emitter to Base Voltage	V _{EBO}	1.5	٧
Collector Current	lc	100	mA
Total Power Dissipation	Ptot Note	190	mW
Junction Temperature	Tj	150	ç
Storage Temperature	T _{stg}	-65 to +150	°C

Note Mounted on 1.08 cm² × 1.0 mm (t) glass epoxy PCB

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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ELECTRICAL CHARACTERISTICS (TA = +25°C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	Ісво	VcB = 5 V, IE = 0 mA	-	-	100	nA
Emitter Cut-off Current	ІЕВО	V _{EB} = 1 V, I _C = 0 mA	ı	ı	100	nA
DC Current Gain	hfE Note 1	Vce = 2 V, Ic = 15 mA	130	190	260	1
RF Characteristics						
Gain Bandwidth Product	f⊤	Vce = 3 V, Ic = 50 mA, f = 2 GHz	14	17	1	GHz
Insertion Power Gain	S _{21e} ²	Vce = 3 V, Ic = 50 mA, f = 2 GHz	11.5	13.5	1	dB
Noise Figure (1)	NF	$\label{eq:Vce} \begin{split} &V_{CE}=2~V,~lc=10~mA,~f=2~GHz,\\ &Z_{S}=Z_{Sopt},~Z_{L}=Z_{Lopt} \end{split}$	_	0.9	1.2	dB
Noise Figure (2)	NF	$\label{eq:Vce} \begin{split} &V_{\text{CE}} = 2 \text{ V, Ic} = 7 \text{ mA, f} = 1 \text{ GHz,} \\ &Z_{\text{S}} = Z_{\text{Sopt}}, \text{ ZL} = Z_{\text{Lopt}} \end{split}$	_	0.6	_	dB
Associated Gain (1)	Ga	$\label{eq:Vce} \begin{split} &V_{CE}=2~V,~I_{C}=10~mA,~f=2~GHz,\\ &Z_{S}=Z_{Sopt},~Z_{L}=Z_{Lopt} \end{split}$	11.0	13.0	_	dB
Associated Gain (2)	Ga	$\label{eq:Vce} \begin{split} &V_{\text{CE}} = 2 \text{ V, Ic} = 7 \text{ mA, f} = 1 \text{ GHz,} \\ &Z_{\text{S}} = Z_{\text{Sopt}}, \ Z_{\text{L}} = Z_{\text{Lopt}} \end{split}$	-	19.0	-	dB
Reverse Transfer Capacitance	Cre Note 2	VcB = 2 V, IE = 0 mA, f = 1 MHz	-	0.4	0.5	pF
Maximum Stable Power Gain	MSG Note 3	Vce = 3 V, Ic = 50 mA, f = 2 GHz	14.5	17.0	1	dB
Gain 1 dB Compression Output Power	Po (1 dB)	$\begin{split} &V_{\text{CE}} = 3.6 \text{ V, Ic }_{(\text{set})} = 10 \text{ mA } \text{(RF OFF)}, \\ &f = 2 \text{ GHz, } Z_{\text{S}} = Z_{\text{Sopt}}, Z_{\text{L}} = Z_{\text{Lopt}} \end{split}$	-	21	-	dBm
Linear Gain	GL	$\label{eq:Vce} \begin{split} &V_{\text{CE}} = 3.6 \text{ V, Ic} = 10 \text{ mA, f} = 2 \text{ GHz,} \\ &Z_{\text{S}} = Z_{\text{Sopt}}, \ Z_{\text{L}} = Z_{\text{Lopt}} \end{split}$	-	15	-	dBm

Notes 1. Pulse measurement: PW \leq 350 μ s, Duty Cycle \leq 2%

2. Collector to base capacitance when the emitter grounded

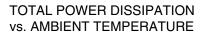
3. MSG =
$$\frac{S_{21}}{S_{12}}$$

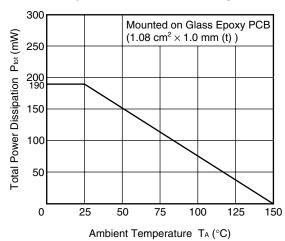
hfe CLASSIFICATION

<R>

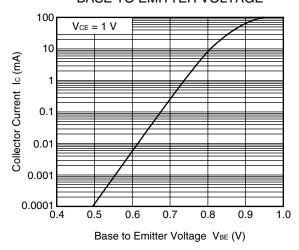
Rank	FB/YFB		
Marking	zH		
h _{FE} Value	130 to 260		

<R> TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

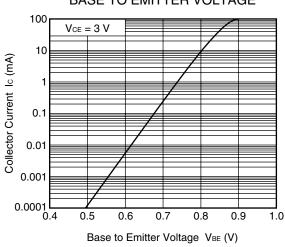




COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

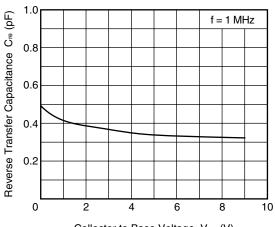


COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



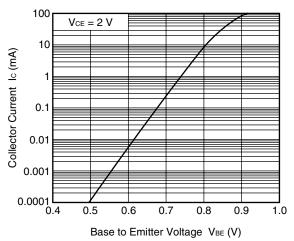
Remark The graphs indicate nominal characteristics.

REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE

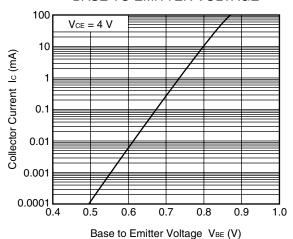


Collector to Base Voltage VcB (V)

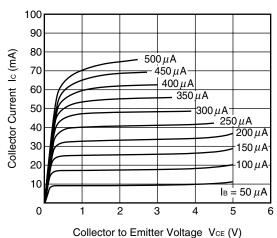
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



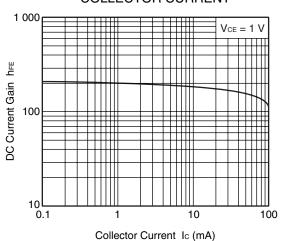
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



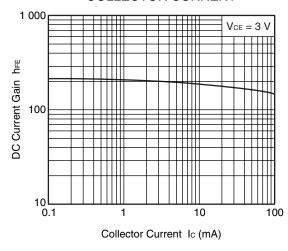
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



DC CURRENT GAIN vs. COLLECTOR CURRENT

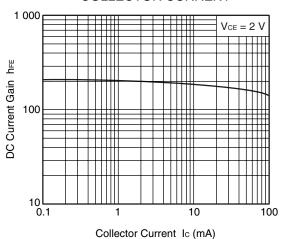


DC CURRENT GAIN vs. COLLECTOR CURRENT

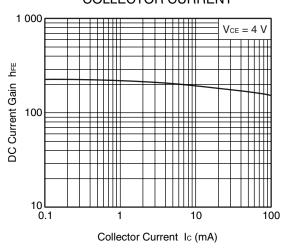


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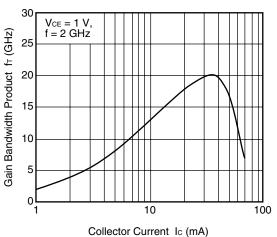
DC CURRENT GAIN vs. COLLECTOR CURRENT



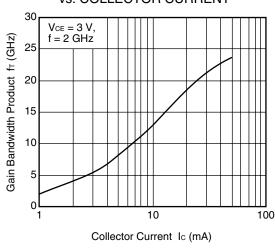
DC CURRENT GAIN vs. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

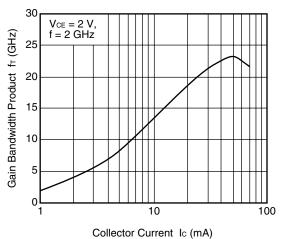


GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

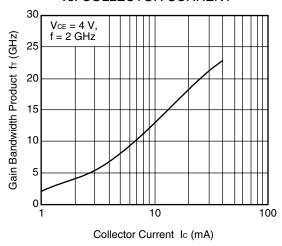


Remark The graphs indicate nominal characteristics.

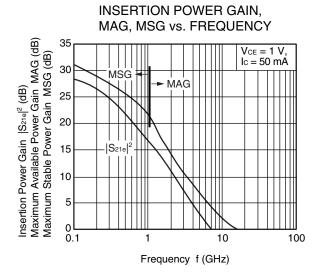
GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

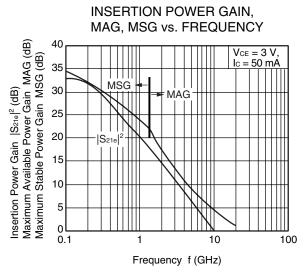


GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

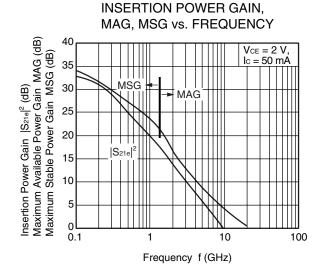


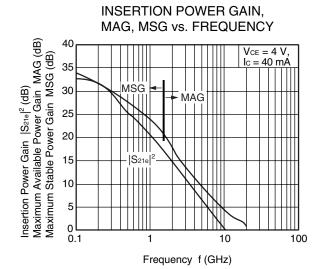
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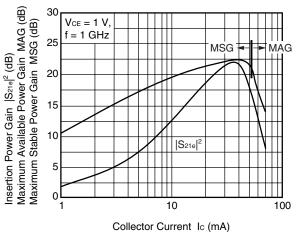


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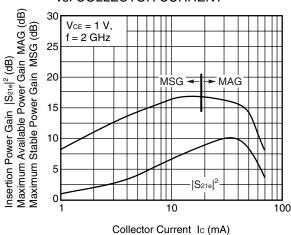




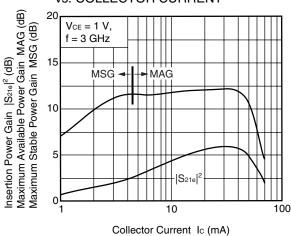
INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT

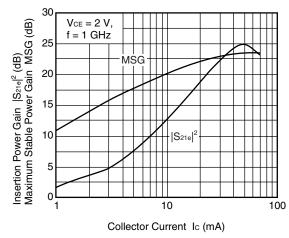


INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT

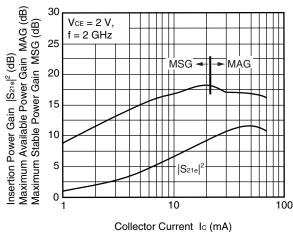


Remark The graphs indicate nominal characteristics.

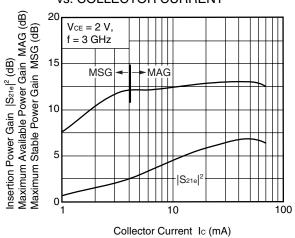
INSERTION POWER GAIN, MSG vs. COLLECTOR CURRENT



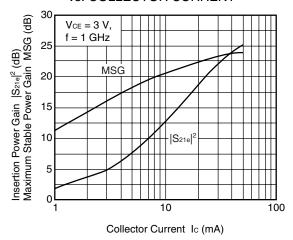
INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



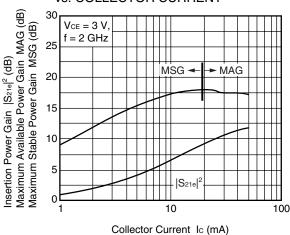
INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



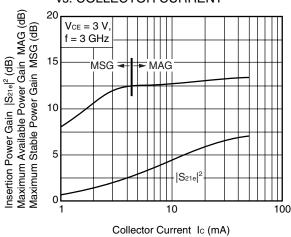
INSERTION POWER GAIN, MSG vs. COLLECTOR CURRENT



INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT

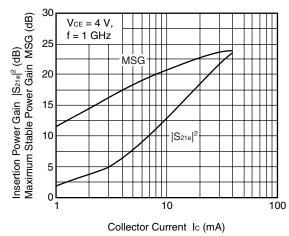


INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT

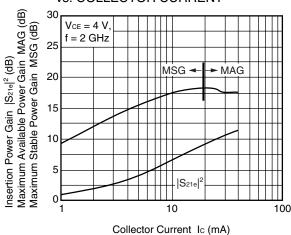


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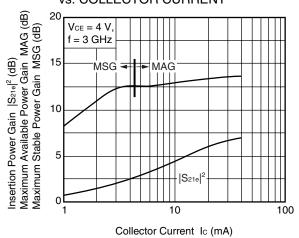
INSERTION POWER GAIN, MSG vs. COLLECTOR CURRENT



INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



-20

-15

-10

COLLECTOR EFFICIENCY vs. INPUT POWER 120 20 100 Output Power Pout (dBm) Power Gain GP (dB) Collector Current lc (mA) Collector Efficiency ηc (%) GР 15 10 60 Pout

 η c

Vce = 3.6 V, f = 1 GHz

5

 $I_{\text{cq}} = 10 \text{ mA}$

0

40

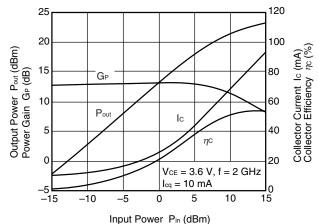
20

10

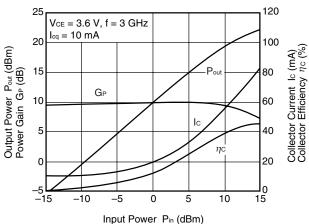
OUTPUT POWER, POWER GAIN, Ic.

-5 Input Power Pin (dBm)

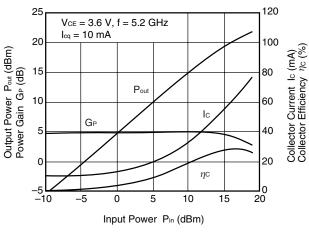
OUTPUT POWER, POWER GAIN, Ic. COLLECTOR EFFICIENCY vs. INPUT POWER



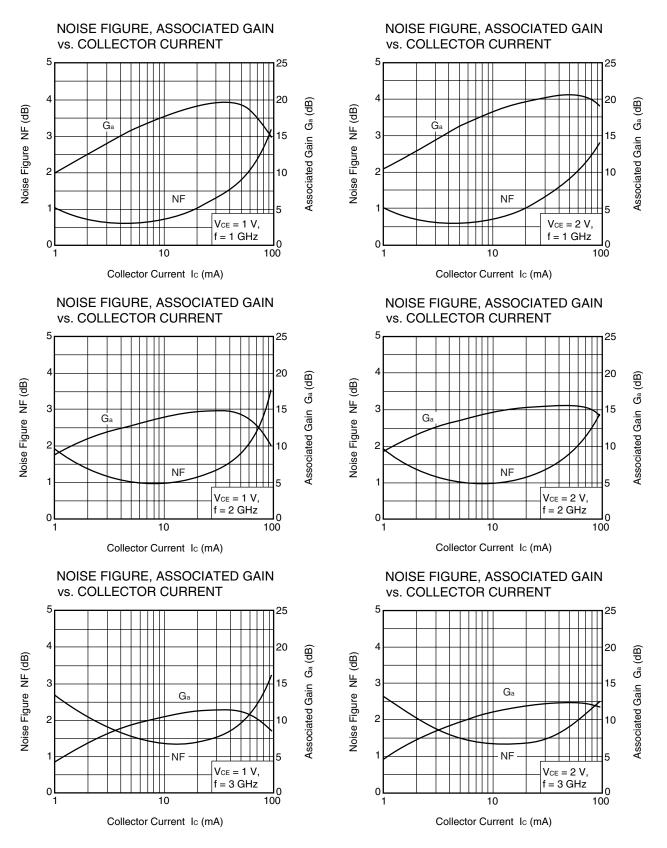
OUTPUT POWER, POWER GAIN, Ic, COLLECTOR EFFICIENCY vs. INPUT POWER



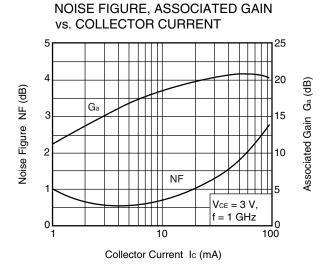
OUTPUT POWER, POWER GAIN, Ic, COLLECTOR EFFICIENCY vs. INPUT POWER

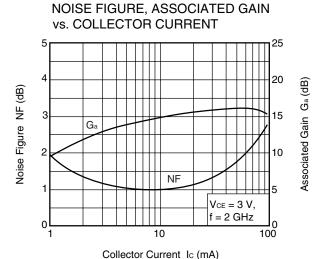


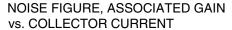
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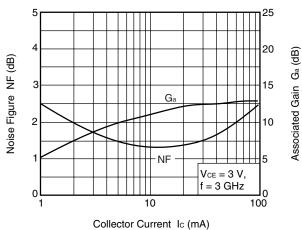


Remark The graphs indicate nominal characteristics.









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<R> S-PARAMETERS

S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.

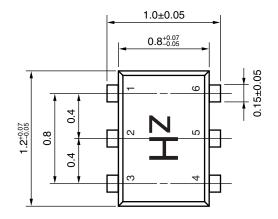
Click here to download S-parameters.

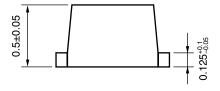
 $[\mathsf{RF} \ \mathsf{and} \ \mathsf{Microwave}] \to [\mathsf{Device} \ \mathsf{Parameters}]$

URL http://www.necel.com/microwave/en/

PACKAGE DIMENSIONS

6-PIN LEAD-LESS MINIMOLD (M16, 1208 PKG) (UNIT: mm)





PIN CONNECTIONS

- 1. Collector
- 2. Emitter
- 3. Emitter
- 4. Base
- 5. Emitter
- 6. Emitter

Caution All four Emitter-pins should be connected to PWB in order to obtain better Electrical performance and heat sinking.

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- "Specific": Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems and medical equipment for life support, etc.

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